

IN THE CLAIMS:

1. (Previously Presented) A method for fabricating a semiconductor device including a capacitor device having a lower electrode, a capacitor dielectric film formed on said lower electrode and an upper electrode formed on said capacitor dielectric film, comprising a step of:

forming a conducting film to be formed into said lower electrode including sub-steps of:

forming a lower conducting film over a substrate by sputtering; and

forming an upper conducting film directly on and in contact with said lower conducting film by CVD.

2. (Original) The method for fabricating a semiconductor device of Claim 1, wherein said lower conducting film has a thickness of 0.5 nm through 5 nm.

3. (Previously Presented) A method for fabricating a semiconductor device including a capacitor device having a lower electrode, a capacitor dielectric film formed on said lower electrode and an upper electrode formed on said capacitor dielectric film, comprising a step of:

forming a conducting film to be formed into said upper electrode including sub-steps of:

forming a lower conducting film over said capacitor dielectric film by sputtering; and

forming an upper conducting film directly on and in contact with said lower conducting film by CVD.

4. (Original) The method for fabricating a semiconductor device of Claim 3, wherein said capacitor device is a concaved capacitor device.

5. (Original) The method for fabricating a semiconductor device of Claim 3, wherein said capacitor device is a stacked capacitor device.

6. (Original) The method for fabricating a semiconductor device of Claim 3,

wherein the CVD is carried out in an oxidizing atmosphere.

7. (Original) The method for fabricating a semiconductor device of Claim 3, wherein said lower conducting film has a thickness of 0.5 nm through 5 nm.
8. (Previously presented) The method for fabricating a semiconductor device of Claim 1, wherein said capacitor device is a concaved capacitor device, and wherein said lower conducting film is formed over an insulating film having a recess formed over said substrate.
9. (Original) The method for fabricating a semiconductor device of Claim 8, wherein said capacitor device is made of a perovskite type high dielectric constant or ferroelectric material.
10. (Original) The method for fabricating a semiconductor device of Claim 3, wherein said capacitor device is made of a perovskite type high dielectric constant or ferroelectric material.
11. (New) The method for fabricating a semiconductor device of Claim 1, wherein said lower conducting film and said upper conducting film are composed of a precious metal or a precious metal alloy.
12. (New) The method for fabricating a semiconductor device of Claim 11, wherein said precious metal is platinum.
13. (New) The method for fabricating a semiconductor device of Claim 3, wherein said lower conducting film and said upper conducting film are composed of a precious metal or a precious metal alloy.

14. (New) The method for fabricating a semiconductor device of Claim 13, wherein said precious metal is platinum.